

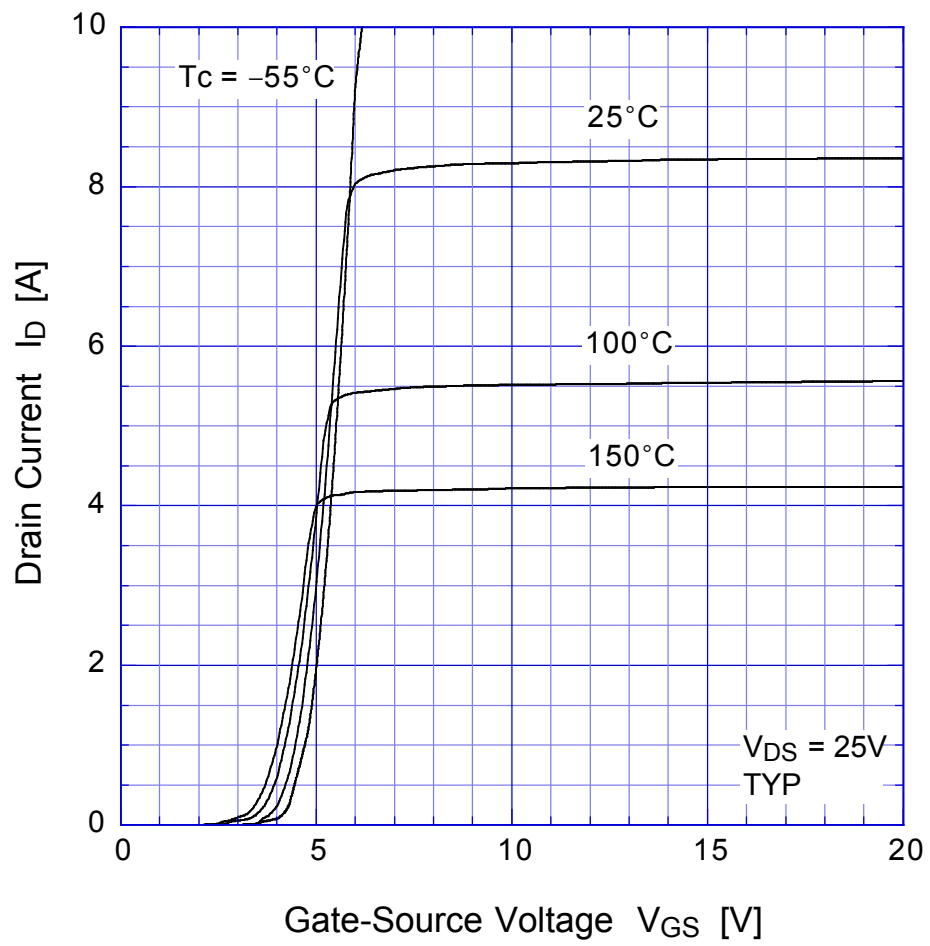


●Electrical Characteristics T<sub>c</sub> = 25°C

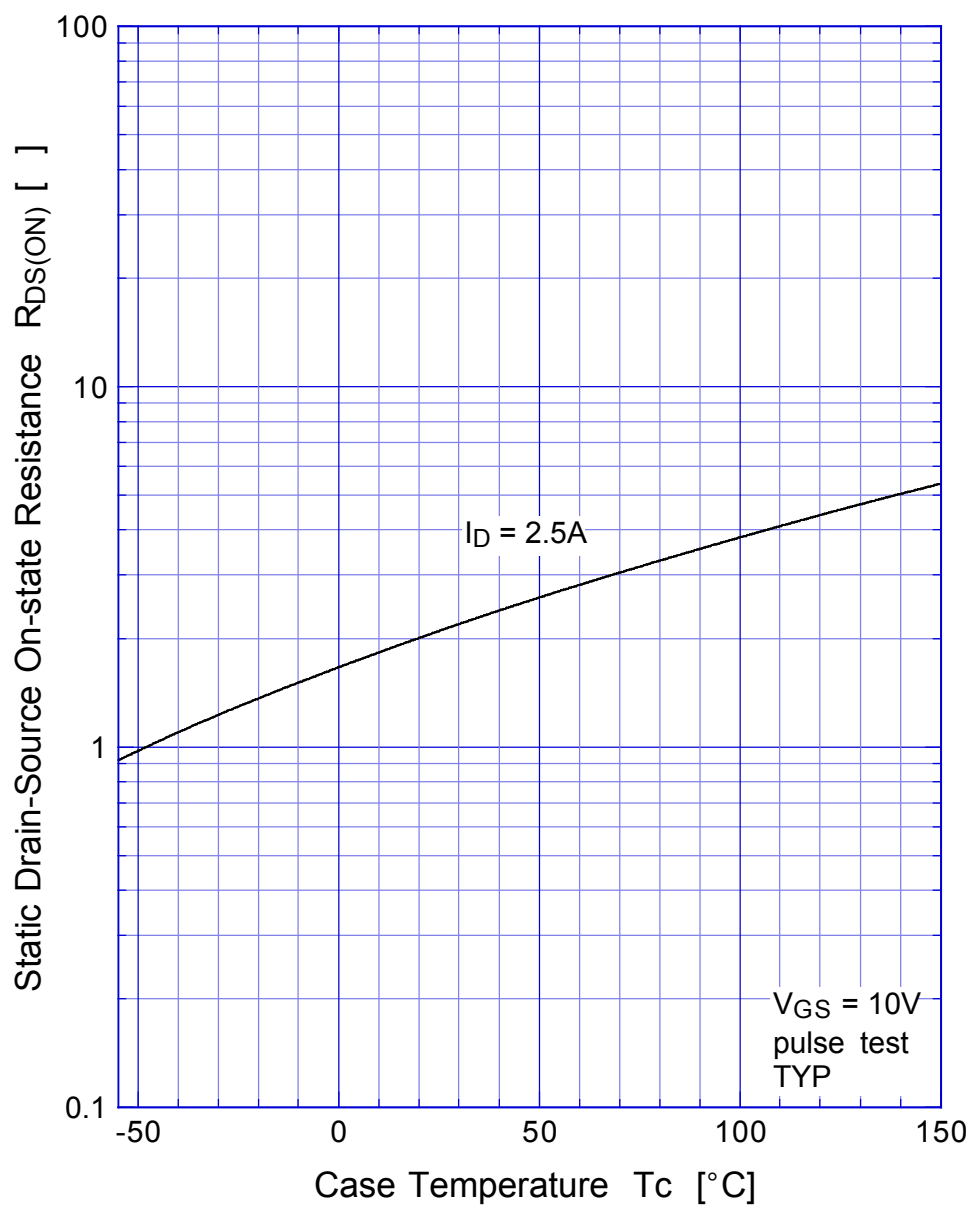
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0V	900			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900V, V <sub>GS</sub> = 0V			250	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±0.1	
Forward Transconductance	g <sub>fs</sub>	I <sub>D</sub> = 2.5A, V <sub>DS</sub> = 10V	2.4	4.0		S
Static Drain-Source On-state Resistance	R <sub>DS(ON)</sub>	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 10V		2.1	2.8	Ω
Gate Threshold Voltage	V <sub>TH</sub>	I <sub>D</sub> = 1mA, V <sub>DS</sub> = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 2.5A, V <sub>GS</sub> = 0V			1.5	
Thermal Resistance	θ <sub>jc</sub>	junction to case			3.12	°C/W
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = 400V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 5A		45		nC
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		1140		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			23		
Output Capacitance	C <sub>oss</sub>			105		
Turn-On Time	t <sub>on</sub>	I <sub>D</sub> = 2.5A, R <sub>L</sub> = 60Ω, V <sub>GS</sub> = 10V		55	100	ns
Turn-Off Time	t <sub>off</sub>			210	350	

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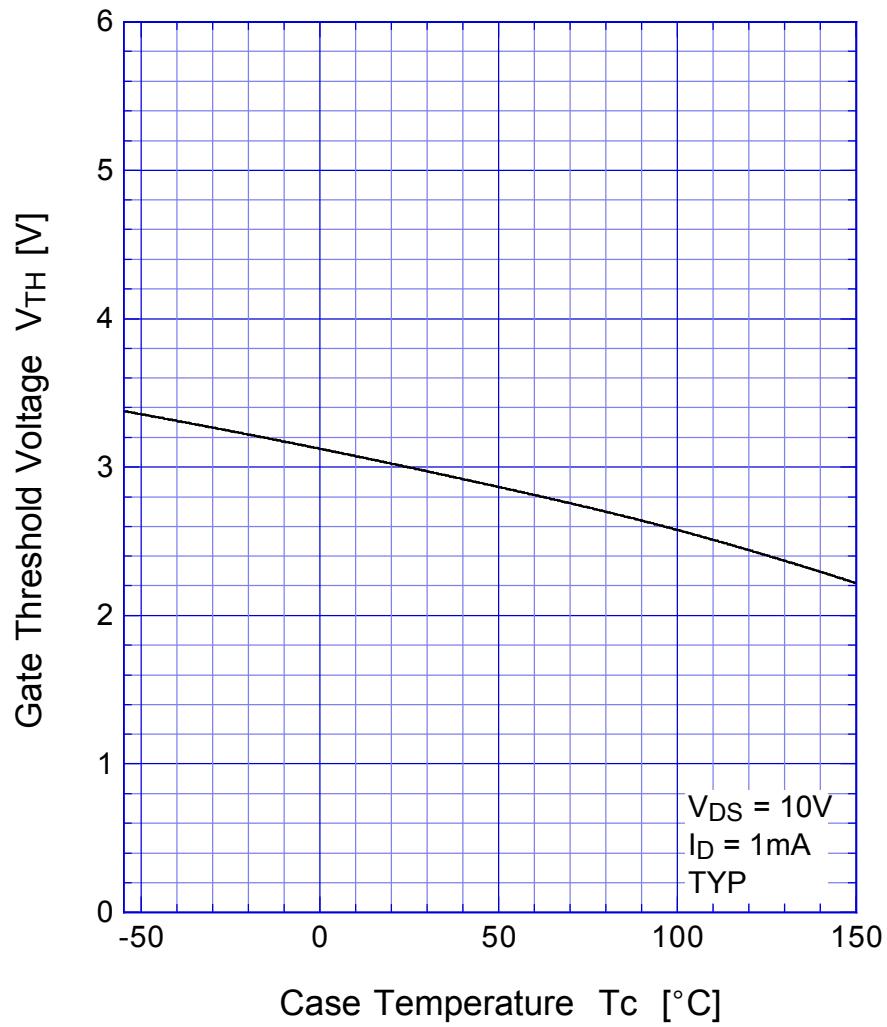
Transfer Characteristics



## 2SK2671 Static Drain-Source On-state Resistance

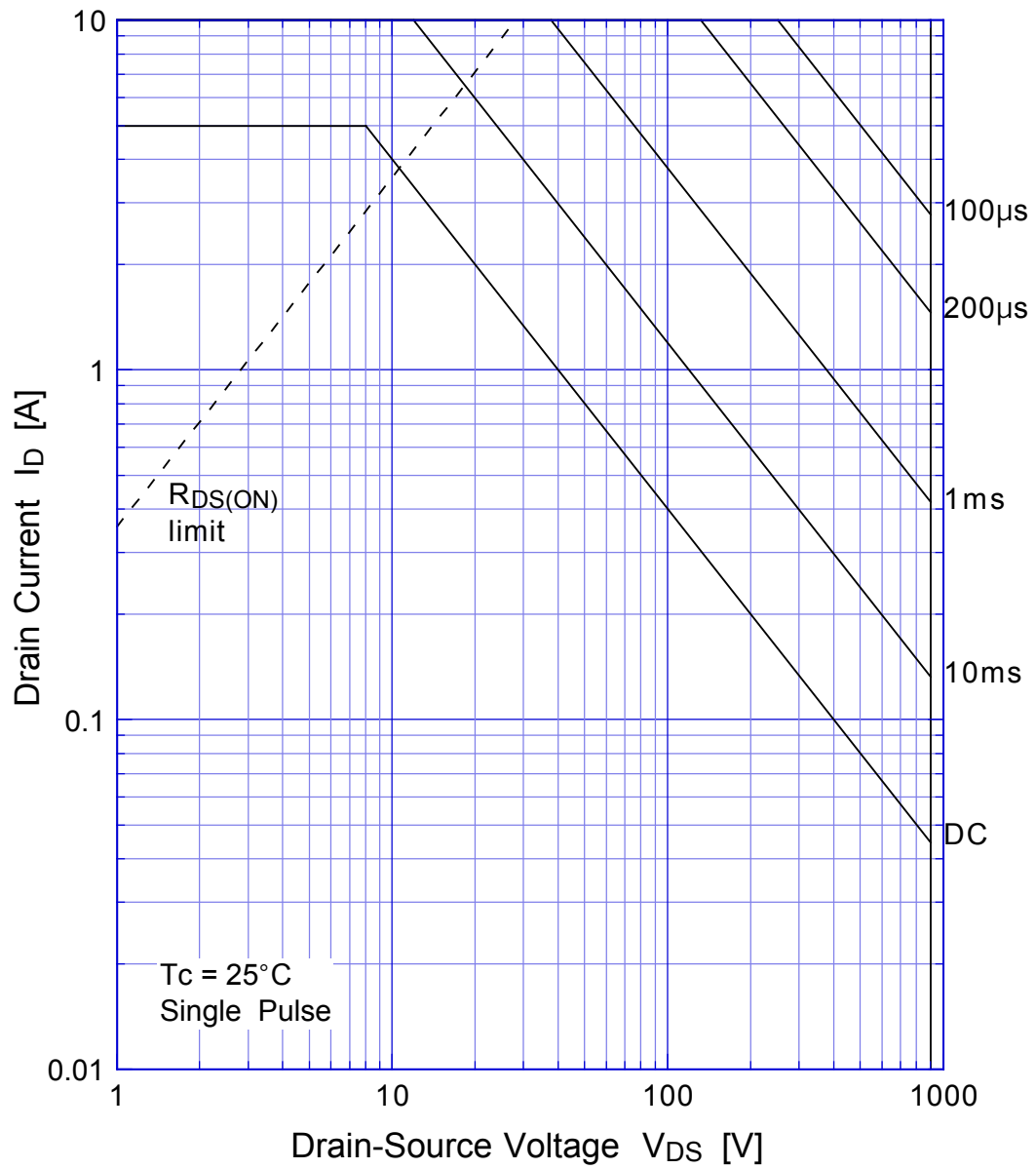


## 2SK2671 Gate Threshold Voltage

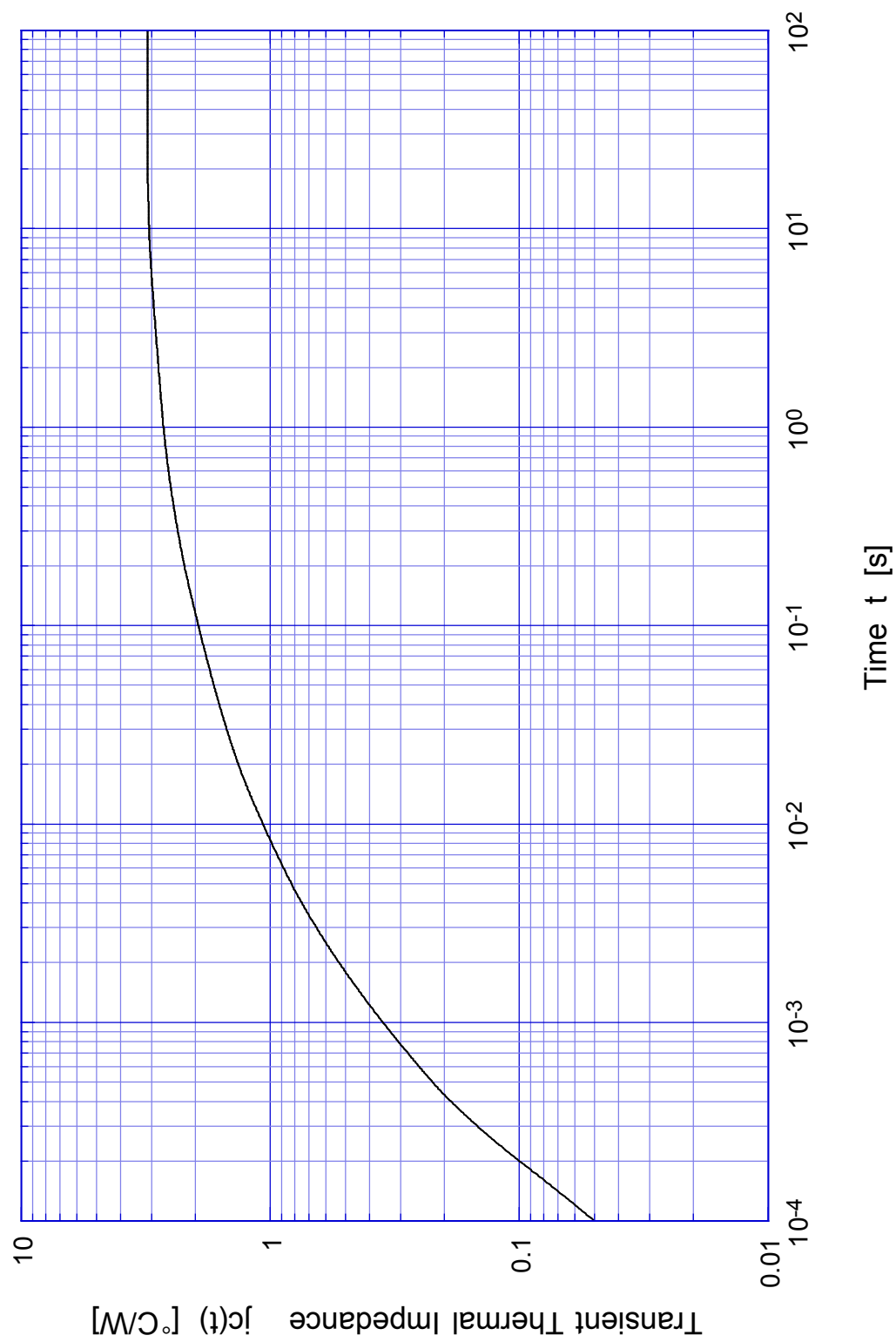


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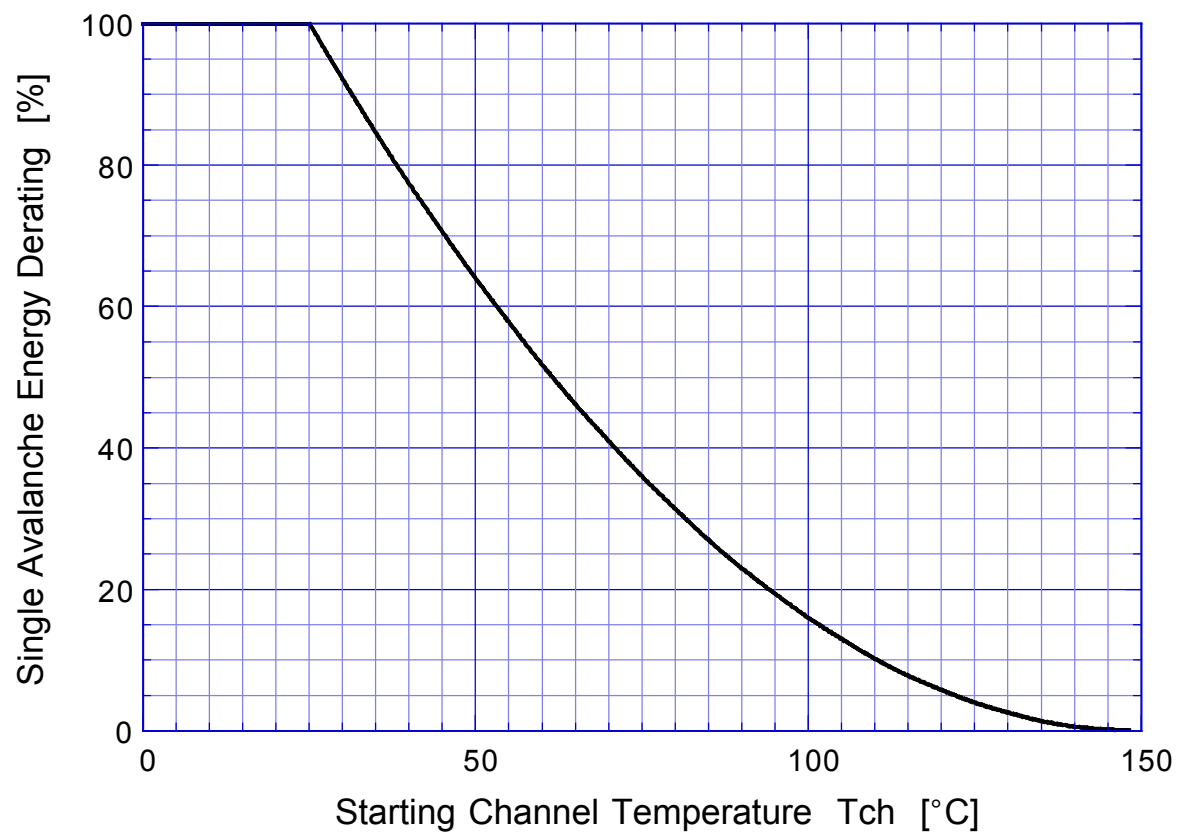
Safe Operating Area



## 2SK2671 Transient Thermal Impedance



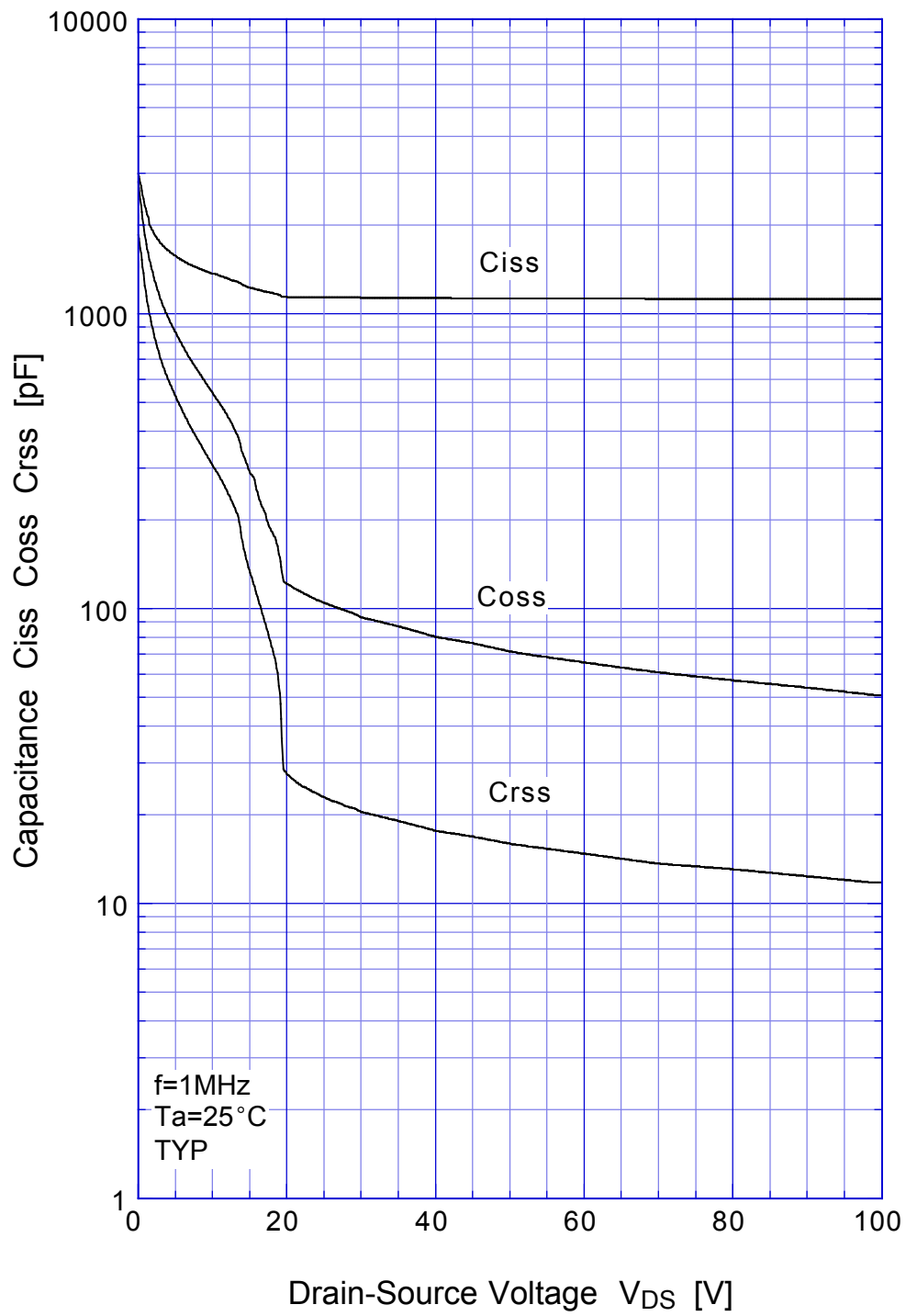
## 2SK2671 Single Avalanche Energy Derating



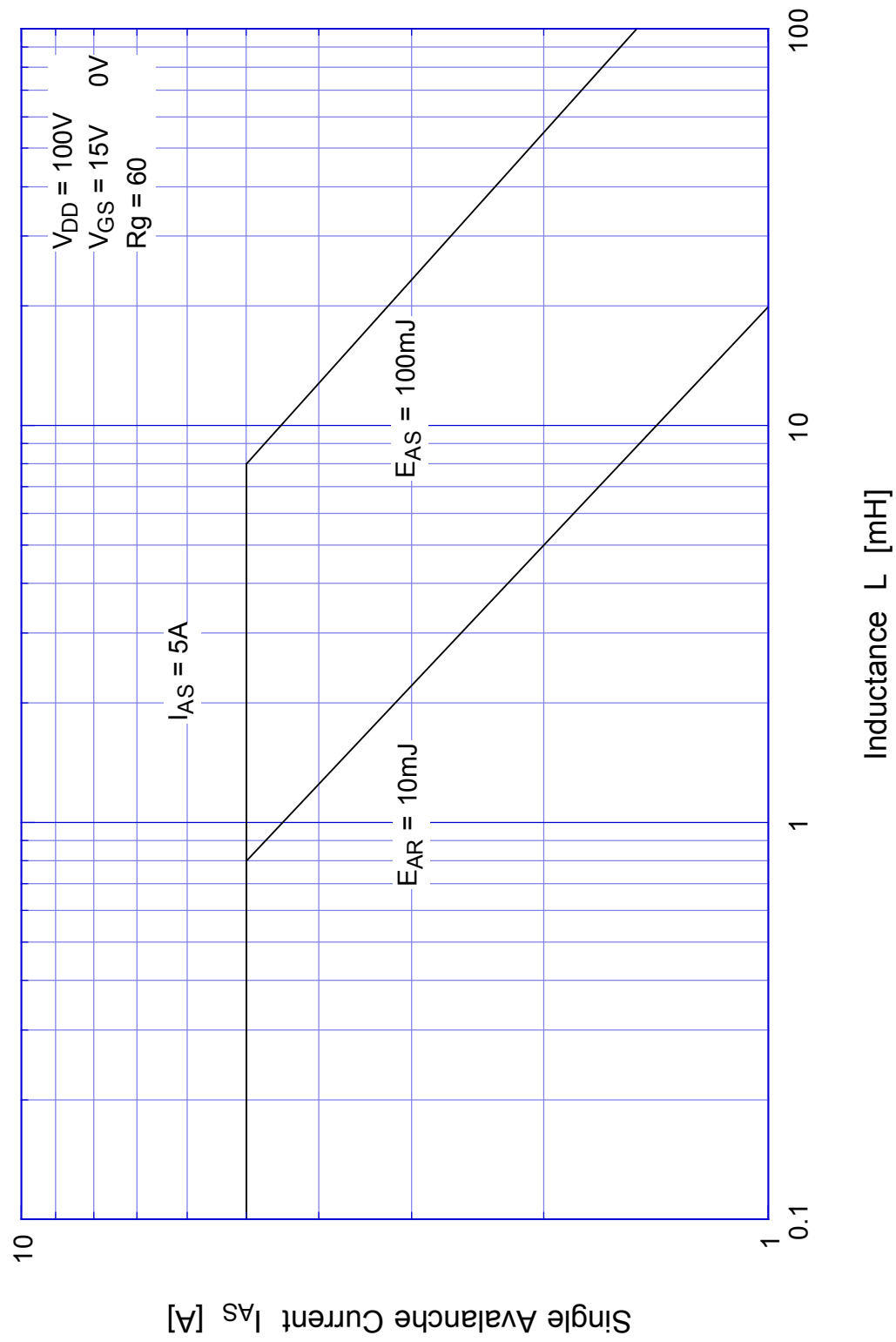


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Capacitance

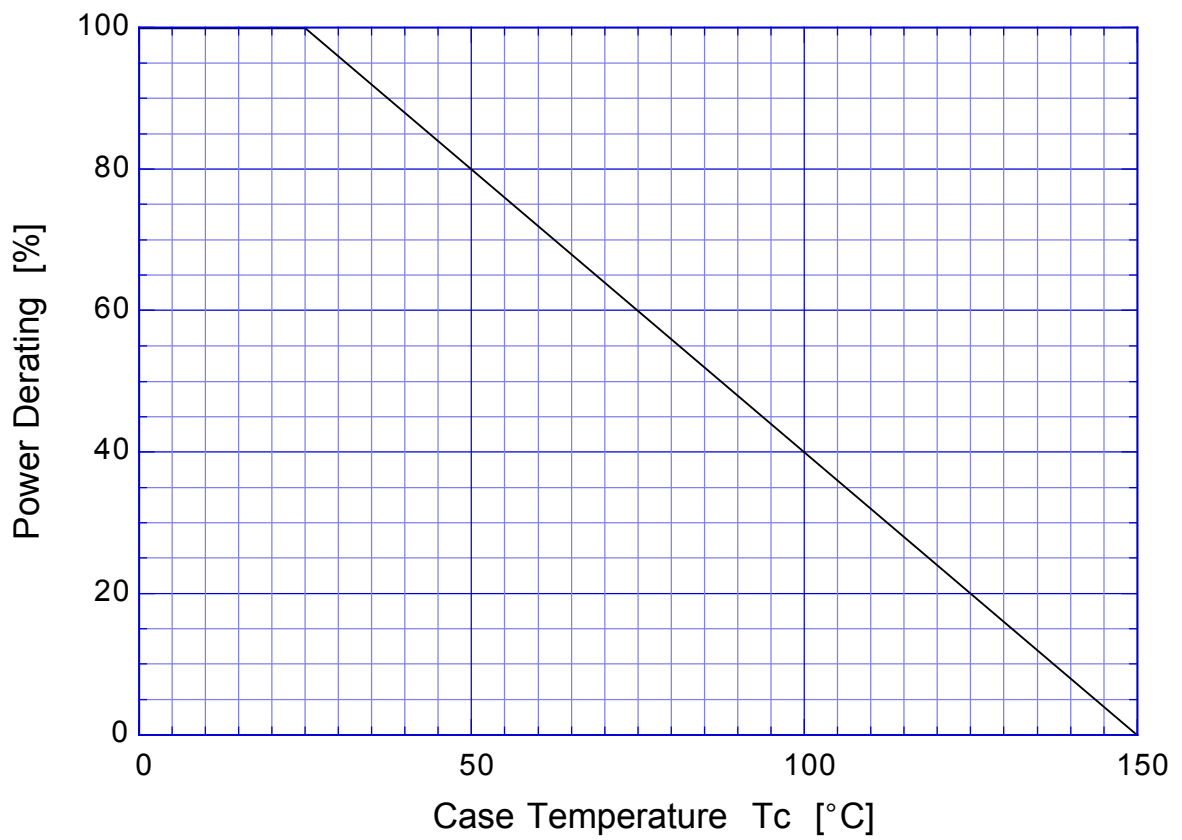


## 2SK2671 Single Avalanche Current - Inductive Load



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Power Derating



## 2SK2671 Gate Charge Characteristics

